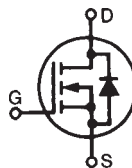


PolarHV™ HiPerFET Power MOSFET

IXFA 16N50P
IXFH 16N50P
IXFP 16N50P

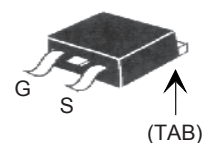
$V_{DSS} = 500 \text{ V}$
 $I_{D25} = 16 \text{ A}$
 $R_{DS(on)} \leq 400 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

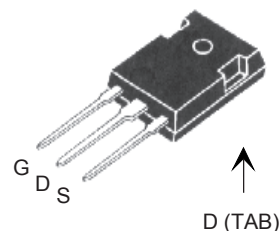


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	16	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	35	A
I_{AR}	$T_C = 25^\circ\text{C}$	16	A
E_{AR}	$T_C = 25^\circ\text{C}$	25	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	750	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 10 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s soldering	260	$^\circ\text{C}$
M_d	Mounting torque (TO-247 & TO-220)	1.13/10	Nm/lb.in.
Weight	TO-220	4	g
	TO-263	3	g
	TO-247	5.5	g

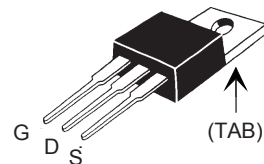
TO-263 (IXTA)



TO-247 (IXFH)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5 \text{ mA}$	3.0		5.5 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			400 $\text{m}\Omega$

Features

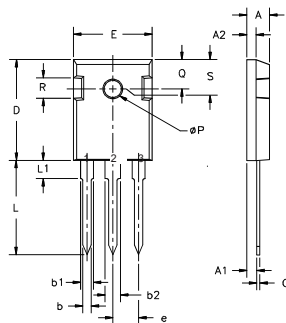
- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

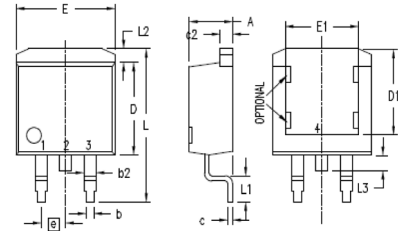
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$, pulse test	8	16	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2250	pF
C_{oss}			240	pF
C_{rss}			12	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_{D25}$ $R_G = 10\ \Omega$ (External)		23	ns
t_r			25	ns
$t_{d(off)}$			70	ns
t_f			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		43	nC
Q_{gs}			15	nC
Q_{gd}			12	nC
R_{thJC}				0.42°C/W
R_{thCS}	(TO-220)		0.25	$^\circ\text{C/W}$
R_{thCS}	(TO-247)		0.21	$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			16 A
I_{SM}	Repetitive			35 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 16\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$		130	200 ns
I_{RM}			6	A
Q_{RM}			0.6	μC

TO-247 (IXFH) Outline


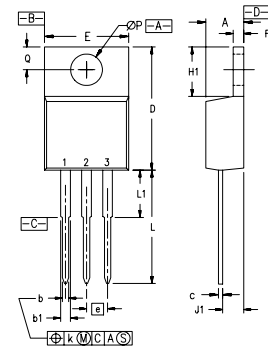
Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-263 (IXTA) Outline


1. GATE (COLLECTOR)
2. DRAIN (COLLECTOR)
3. SOURCE (EMITTER)
4. DRAIN (COLLECTOR) BOTTOM SIDE

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A ₁	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b ₂	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c ₂	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D ₁	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E ₁	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L ₁	.090	.110	2.29	2.79
L ₂	.040	.055	1.02	1.40
L ₃	.050	.070	1.27	1.78
L ₄	0	.005	0	0.13

TO-220 (IXTP) Outline


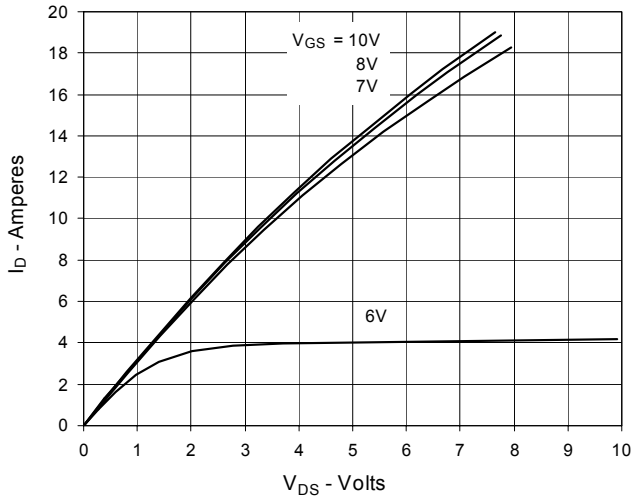
Pins: 1 - Gate 2 - Drain
3 - Source 4 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b ₁	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H ₁	.230	.270	5.85	6.85
J ₁	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L ₁	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

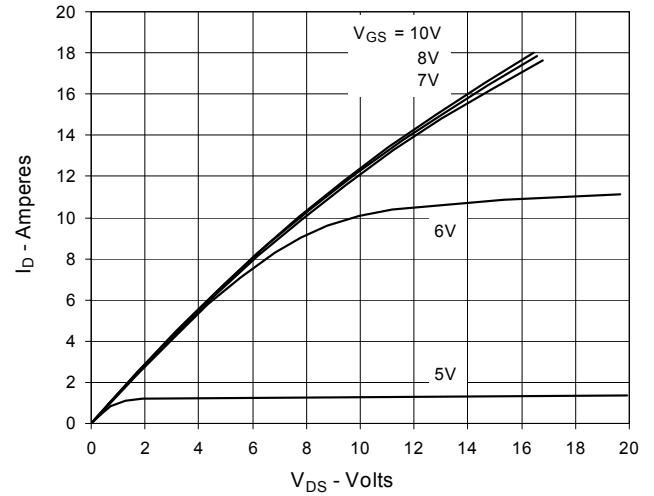
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585
one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

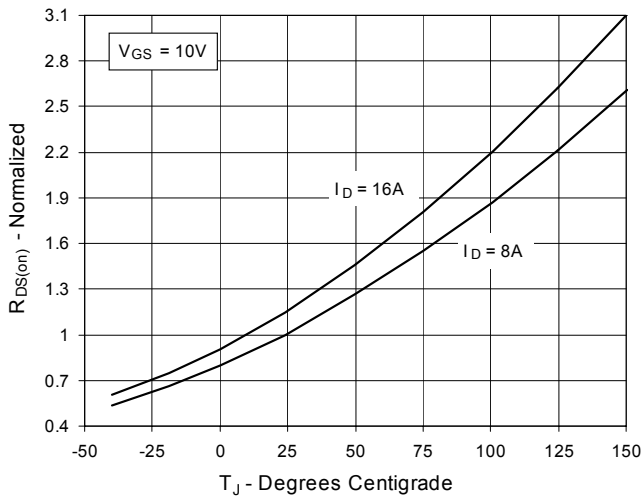
**Fig. 1. Output Characteristics
@ 25°C**



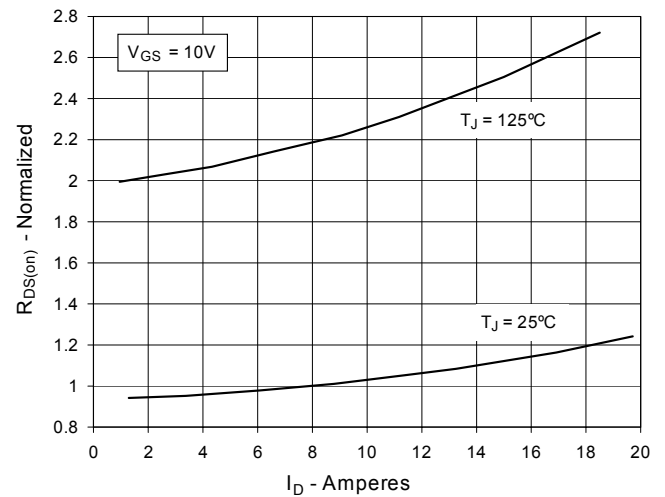
**Fig. 2. Output Characteristics
@ 125°C**



**Fig. 3. $R_{DS(on)}$ Normalized to $I_D = 8A$ vs.
Junction Temperature**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 8A$ vs. Drain
Current**



**Fig. 5. Maximum Drain Current vs.
Case Temperature**

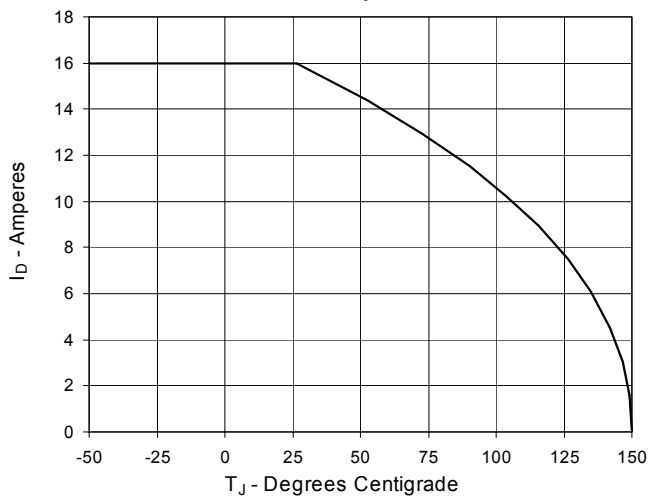


Fig. 6. Input Admittance

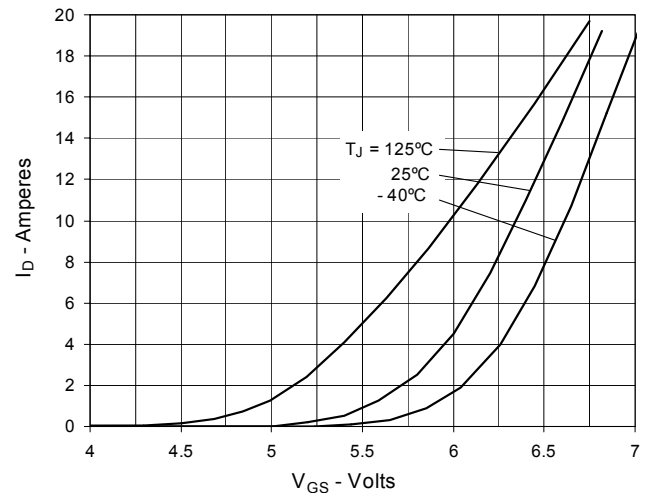


Fig. 7. Transconductance

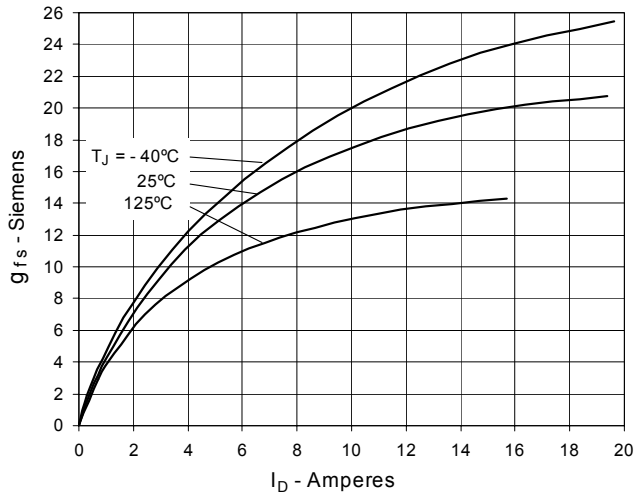


Fig. 8. Forward Voltage Drop of Intrinsic Diode

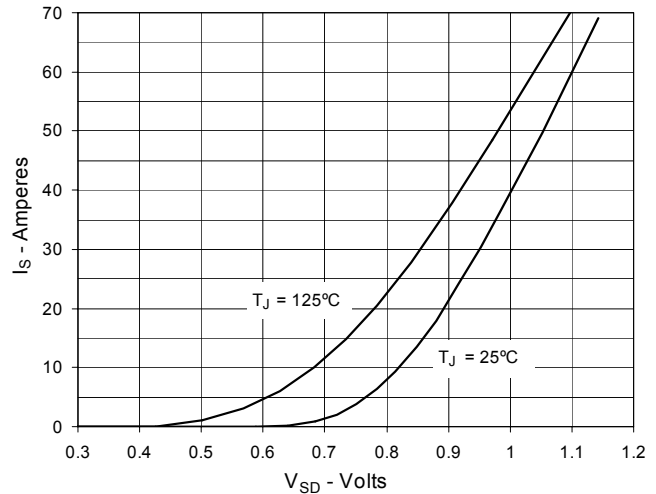


Fig. 9. Gate Charge

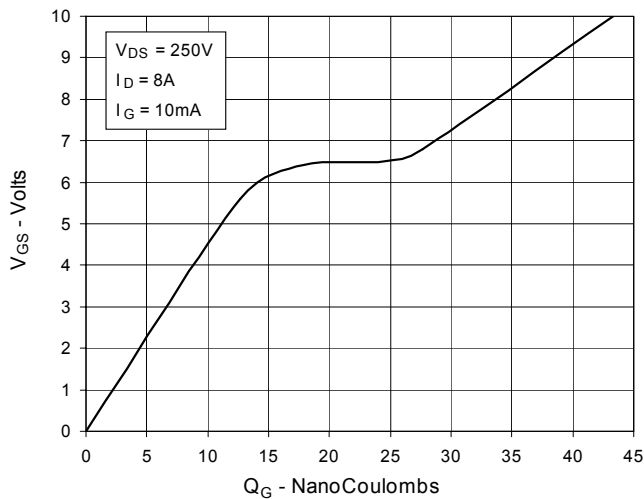


Fig. 10. Capacitance

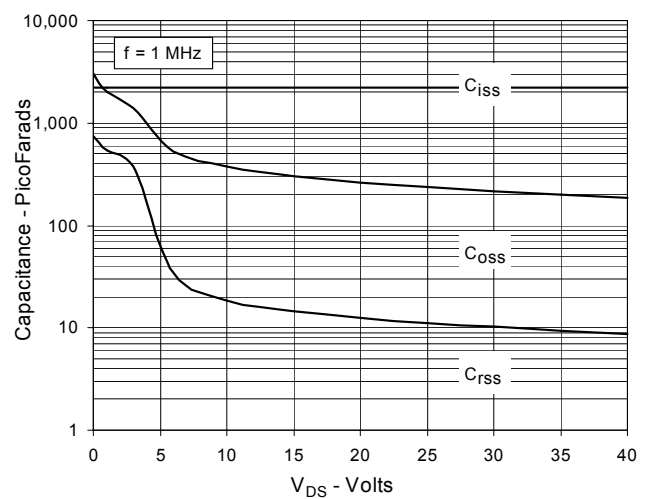


Fig. 11. Forward-Bias Safe Operating Area

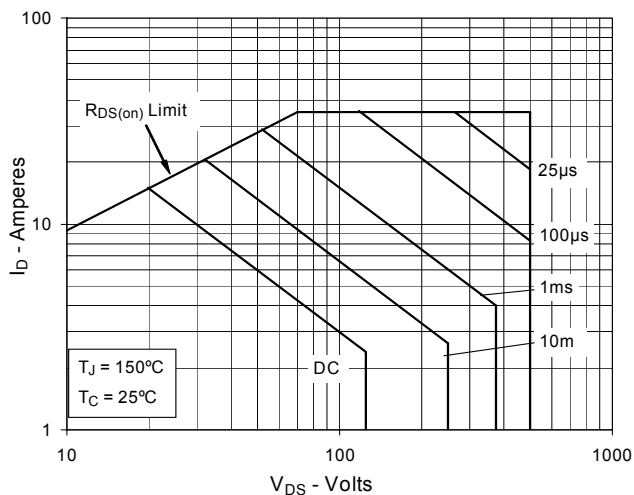


Fig. 12. Maximum Transient Thermal Resistance

